

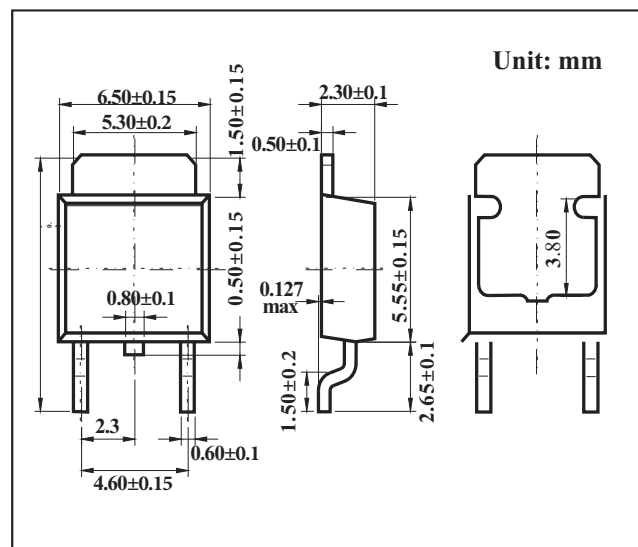
TO-252 Plastic-Encapsulate Transistors

FEATURES

- PNP TRANSISTORS
- Collector-Base Voltage: $V_{CBO}=-40V$
- Low Speed Switching

MECHANICAL DATA

- Case style:TO-252 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

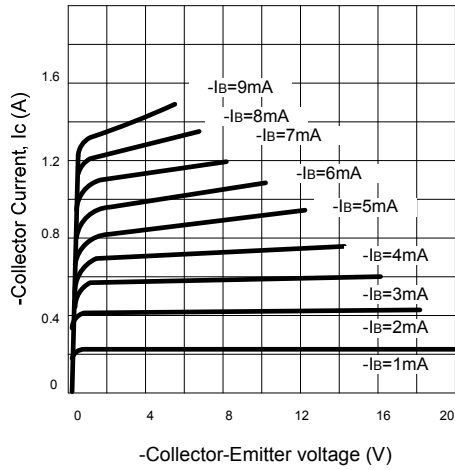
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current -Continuous	I_C	-3	A
Collector Power Dissipation	P_C	1.25	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	100	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C

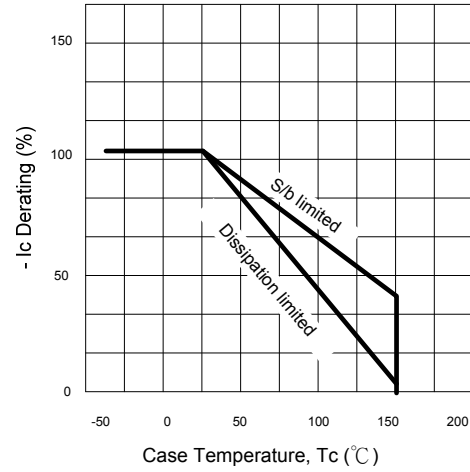
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-30V, I_B=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C=-1A$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1.5	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-0.1A$ $f=10MHz$	50	80		MHz

RATINGS AND CHARACTERISTIC CURVES

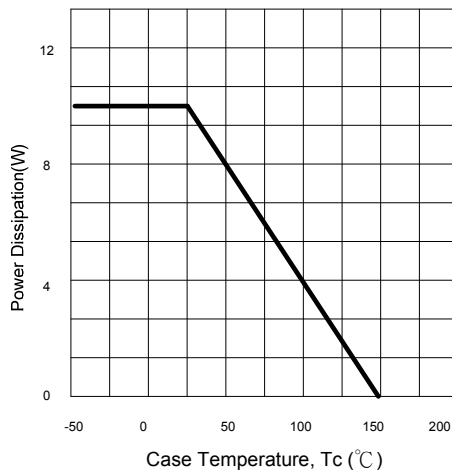
Static Characteristics



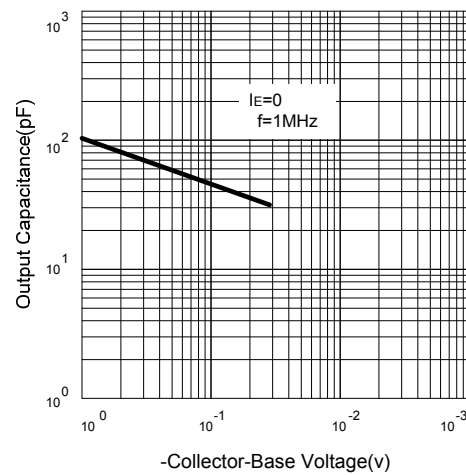
Derating Curve of Safe Operating Areas



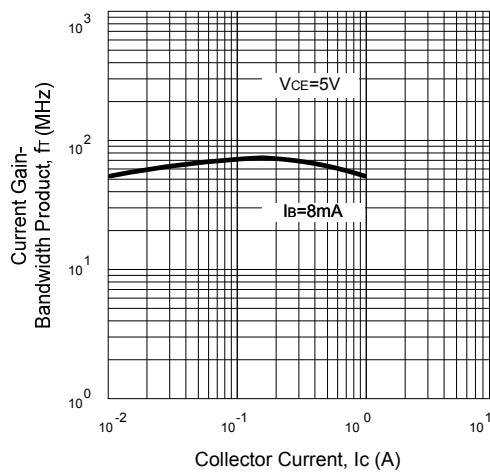
Power Derating



Collector Output Capacitance



Current Gain-Bandwidth Product



Safe Operating Area

